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TOWNSEND and TOWNSEND and CREW LLP

By: T. Matthew

PATENT
Attorney Docket No.: 015114-047930US
Client Ref. No.: A293-D1

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

Raminda U. Madurawe et al.

Application No.: 09/606,252

Filed: June 28, 2000

For: HIGH VOLTAGE MOS DEVICES WITH HIGH GATED-DIODE BREAKDOWN VOLTAGE AND PUNCH-THROUGH VOLTAGE

Examiner: Paul E. Brock II

Art Unit: 2815

AMENDMENT

FAX COPY RECEIVED
OCT 15 2002
TECHNOLOGY CENTER 2800

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

In response to the office action mailed April 15, 2002, please amend the above-identified application as follows:

IN THE CLAIMS:

Please cancel claims 21-26, 39, and 41 without prejudice. Please amend claims 27, 31, and 38 as indicated. Please add new claims 42-44.

27. (Amended) A method of fabricating a transistor in an integrated circuit device comprising:

providing a semiconductor substrate;

forming a gate xide on the semiconductor substrate;

forming a gate on the gate xide;

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